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FSB52006S

Motion SPM® 5 系列

2014 年 10 月



特性

- 通过 UL 第 E209204 号认证 (UL1557)
- 60 V $R_{DS(on)} = 80 \text{ m}\Omega$ (最大值) FRFET MOSFET 三相逆变器, 带有栅极驱动器
- 低端 MOSFET 的三个独立开源引脚用于三相电流感测
- 高电平有效接口, 可用于 3.3 / 5 V 逻辑电平, 施密特触发脉冲输入
- 针对低电磁干扰进行优化
- 用于栅极驱动和欠压保护的 HVIC
- 绝缘等级: 1500 V_{rms} / 分钟
- 湿度敏感等级 (MSL) 3
- 符合 RoHS 标准

应用

- 小功率交流电机驱动器的三相逆变器驱动

相关资料

- [AN-9082 - Motion SPM5 Series Thermal Performance by Contact Pressure](#)
- [AN-9080 - User's Guide for Motion SPM 5 Series Ver.1](#)

概述

FSB52006S 是一款先进的 Motion SPM® 5 模块, 为交流感应、无刷直流电机和 PMSM 电机提供非常全面的高性能逆变器输出平台。这些模块综合优化了内置 MOSFET (FRFET® 技术) 的栅极驱动以最小化电磁干扰和能量损耗。内置的高速 HVIC 只需要一个单电源电压, 将逻辑电平栅极输入转化为适合驱动模块内部 MOSFET 的高电压, 高电流驱动信号。独立的开源 MOSFET 端子在每个相位均有效, 可支持大量不同种类的控制算法。



封装标识与订购信息

器件标识	器件	封装	卷尺寸	包装类型	数量
FSB52006S	FSB52006S	SPM5D-023	330 mm	卷带和卷盘	450

绝对最大额定值

逆变器部分 (单个 MOSFET, 除非另有说明。)

符号	参数	工作条件	额定值	单位
V_{DSS}	单个 MOSFET 的漏极 - 源极电压		60	V
$*I_{D25}$	单个 MOSFET 的漏极持续电流	$T_C = 25^\circ\text{C}$	2.6	A
$*I_{D80}$	单个 MOSFET 的漏极持续电流	$T_C = 80^\circ\text{C}$	1.3	A
$*I_{DP}$	单个 MOSFET 的漏极峰值电流	$T_C = 25^\circ\text{C}$, $PW < 100 \mu\text{s}$	5.0	A
$*P_D$	最大功耗	$T_C = 25^\circ\text{C}$, 单个 MOSFET	11	W

控制部分 (单个 HVIC, 除非另有说明。)

符号	参数	工作条件	额定值	单位
V_{CC}	控制电源电压	施加在 V_{CC} 和 COM 之间	20	V
V_{BS}	高端偏压	施加在 V_B 和 V_S 之间	20	V
V_{IN}	输入信号电压	施加在 IN 和 COM 之间	$-0.3 \sim V_{CC} + 0.3$	V

热阻

符号	参数	工作条件	额定值	单位
$R_{\theta JC}$	结点-壳体的热阻	逆变器工作条件下的单个 MOSFET (注 1)	9.2	$^\circ\text{C}/\text{W}$

整个系统

符号	参数	工作条件	额定值	单位
T_J	工作结温		$-20 \sim 150$	$^\circ\text{C}$
T_{STG}	存储温度		$-50 \sim 150$	$^\circ\text{C}$
V_{ISO}	绝缘电压	60 Hz, 正弦波形, 1 分钟, 连接陶瓷基板到引脚	1500	V_{rms}

注:

- 关于壳体温度 (T_C) 的测量点, 参见图 4。
- 标记为 "*" 的为计算值或设计因素。

引脚描述

引脚号	引脚名	引脚描述
1	COM	IC 公共电源接地
2	$V_{B(U)}$	U 相高端 MOSFET 驱动的偏压
3	$V_{CC(U)}$	U 相 IC 和低端 MOSFET 驱动的偏压
4	$IN_{(UH)}$	U 相高端的信号输入
5	$IN_{(UL)}$	U 相低端的信号输入
6	$V_{S(U)}$	U 相高端 MOSFET 驱动的偏压接地
7	$V_{B(V)}$	V 相高端 MOSFET 驱动的偏压
8	$V_{CC(V)}$	V 相 IC 和低端 MOSFET 驱动的偏压
9	$IN_{(VH)}$	V 相高端的信号输入
10	$IN_{(VL)}$	V 相低端的信号输入
11	$V_{S(V)}$	V 相高端 MOSFET 驱动的偏压接地
12	$V_{B(W)}$	W 相高端 MOSFET 驱动的偏压
13	$V_{CC(W)}$	W 相 IC 和低端 MOSFET 驱动的偏压
14	$IN_{(WH)}$	W 相高端的信号输入
15	$IN_{(WL)}$	W 相低端的信号输入
16	$V_{S(W)}$	W 相高端 MOSFET 驱动的偏压接地
17	P	直流输入正端
18	U	U 相输出
19	N_U	U 相的直流输入负端
20	N_V	V 相的直流输入负端
21	V	V 相输出
22	N_W	W 相的直流输入负端
23	W	W 相输出

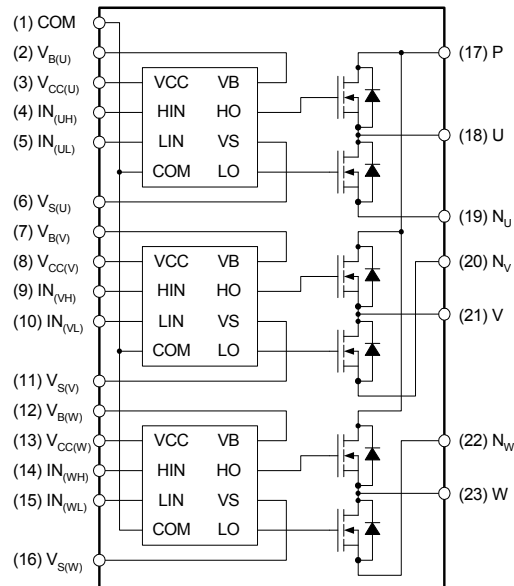


图 1. 引脚布局和内部框图 (仰视图)

注:

3. 每个低端 MOSFET 的源极端子与 Motion SPM® 5 中的电源接地或偏压接地不连接。外部连接应当如图 3 所示。

电气特性 ($T_J = 25^\circ\text{C}$, $V_{CC} = V_{BS} = 15\text{V}$, 除非另有说明。)**逆变器部分** (单个 MOSFET, 除非另有说明。)

符号	参数	工作条件	最小值	典型值	最大值	单位
BV_{DSS}	漏极-源极击穿电压	$V_{IN} = 0\text{V}$, $I_D = 250\ \mu\text{A}$ (注 1)	60	-	-	V
I_{DSS}	零栅极电压漏极电流	$V_{IN} = 0\text{V}$, $V_{DS} = 60\text{V}$	-	-	1	μA
$R_{DS(on)}$	漏极至源极静态导通电阻	$V_{CC} = V_{BS} = 15\text{V}$, $V_{IN} = 5\text{V}$, $I_D = 2.2\text{A}$	-	-	0.08	Ω
V_{SD}	漏极-源极二极管正向电压	$V_{CC} = V_{BS} = 15\text{V}$, $V_{IN} = 0\text{V}$, $I_D = -2.2\text{A}$	-	-	1.0	V
t_{ON}	开关时间	$V_{PN} = 45\text{V}$, $V_{CC} = V_{BS} = 15\text{V}$, $I_D = 2.2\text{A}$ $V_{IN} = 0\text{V} \leftrightarrow 5\text{V}$, 电感负载 $L = 3\text{mH}$ 高端和低端 MOSFET 开关 (注 2)	-	620	-	ns
t_{OFF}			-	360	-	ns
t_{rr}			-	70	-	ns
E_{ON}			-	40	-	μJ
E_{OFF}			-	5	-	μJ
RBSOA	反向偏压安全工作区	$V_{PN} = 55\text{V}$, $V_{CC} = V_{BS} = 15\text{V}$, $I_D = I_{DP}$, $V_{DS} = BV_{DSS}$, $T_J = 150^\circ\text{C}$ 高端和低端 MOSFET 开关 (注 3)	整个区域			

控制部分 (单个 HVIC, 除非另有说明。)

符号	参数	工作条件	最小值	典型值	最大值	单位		
I_{QCC}	V_{CC} 静态电流	$V_{CC} = 15\text{V}$, $V_{IN} = 0\text{V}$	施加在 V_{CC} 和 COM 之间		-	-	160	μA
I_{QBS}	V_{BS} 静态电流	$V_{BS} = 15\text{V}$, $V_{IN} = 0\text{V}$	施加在 $V_{B(U)} - U$, $V_{B(V)} - V$, $V_{B(W)} - W$		-	-	100	μA
UV_{CCD}	低端欠压保护 (图 8)	V_{CC} 欠压保护检测电平		7.4	8.0	9.4	V	
UV_{CCR}		V_{CC} 欠压保护复位电平		8.0	8.9	9.8	V	
UV_{BSD}	高端欠压保护 (图 9)	V_{BS} 欠压保护检测电平		7.4	8.0	9.4	V	
UV_{BSR}		V_{BS} 欠压保护复位电平		8.0	8.9	9.8	V	
V_{IH}	导通阈值电压	逻辑高电平	施加在 IN 和 COM 之间		3.0	-	-	V
V_{IL}	关断阈值电压	逻辑低电平			-	-	0.8	V
I_{IH}	输入偏置电流	$V_{IN} = 5\text{V}$	施加在 IN 和 COM 之间		-	10	20	μA
I_{IL}		$V_{IN} = 0\text{V}$			-	-	2	μA

注:

- BV_{DSS} 是 Motion SPM® 5 产品中的单个 MOSFET 的漏极和源极端子之间的绝对最大额定电压。考虑到寄生电感, V_{PN} 应远低于该值, 因此 V_{PN} 在任何情况下不得超过 BV_{DSS} 。
- t_{ON} 和 t_{OFF} 包括内部驱动 IC 的传输延迟。所列出的数值是在实验室测试条件下测得, 在实际应用中因为印刷电路板和布线的差异, 数值也会有所不同。请查阅图 4 介绍的开关时间定义, 以及图 5 中的开关测试电路。
- 每个 MOSFET 在开关工作时的峰值电流和电压也应在安全工作区 (SOA) 的范围内。请查阅图 5 中的 RBSOA 测试电路, 与开关测试电路相同。

推荐工作条件

符号	参数	工作条件	最小值	典型值	最大值	单位
V_{PN}	电源电压	施加在 P 和 N 之间	-	45	55	V
V_{CC}	控制电源电压	施加在 V_{CC} 和 COM 之间	13.5	15.0	16.5	V
V_{BS}	高端偏压	施加在 V_B 和 V_S 之间	13.5	15.0	16.5	V
$V_{IN(ON)}$	输入导通阈值电压	施加在 IN 和 COM 之间	3.0	-	V_{CC}	V
$V_{IN(OFF)}$	输入关断阈值电压		0	-	0.6	V
t_{dead}	防止桥臂直通的死区时间	$V_{CC} = V_{BS} = 13.5 \sim 16.5 \text{ V}, T_J \leq 150^\circ\text{C}$	1.0	-	-	μs
f_{PWM}	PWM 开关频率	$T_J \leq 125^\circ\text{C}$	-	15	-	kHz
T_C	壳体温度	$T_J \leq 125^\circ\text{C}$	-20	-	100	$^\circ\text{C}$

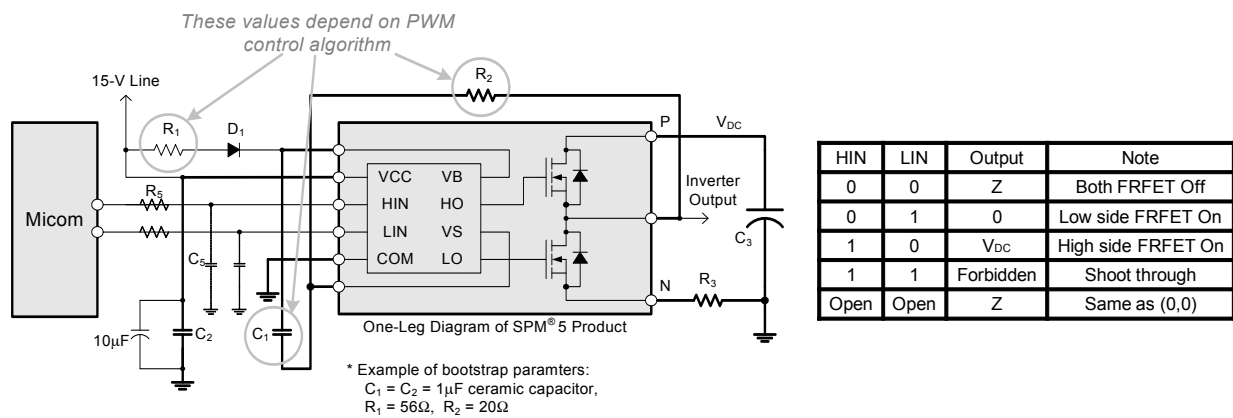


图 2. 推荐的 MCU 接口和自举电路及其参数

注:

1. 推荐的自举二极管 D_1 具有软关断和快速恢复特性，额定电压为 100 V。
2. 自举电路的参数取决于 PWM 算法。上述为开关频率为 15 kHz 时的参数的典型例子。
3. Motion SPM 5 产品和 MCU（虚线显示部分）的每个输入端的 RC 耦合（ R_5 和 C_5 ）和 C_4 可用于防止由浪涌噪声产生的错误信号。
4. 印刷电路板图形中的粗线应尽量短且粗，以减少电路中的寄生电感，从而导致浪涌电压的降低。旁路电容 C_1, C_2 和 C_3 应具有良好的高频特性，以吸收高频纹波电流。

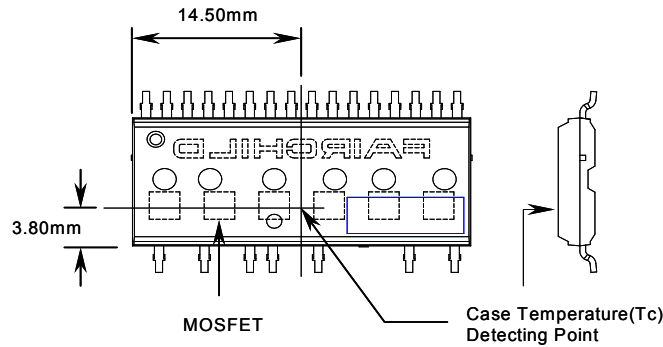


图 3. 壳体温度测量

注:

5. 将热电偶贴在 SPM 5 封装（如果应用到，放在 SPM 5 封装和散热片中间）的散热片的顶部，以获得正确的温度测量数值。

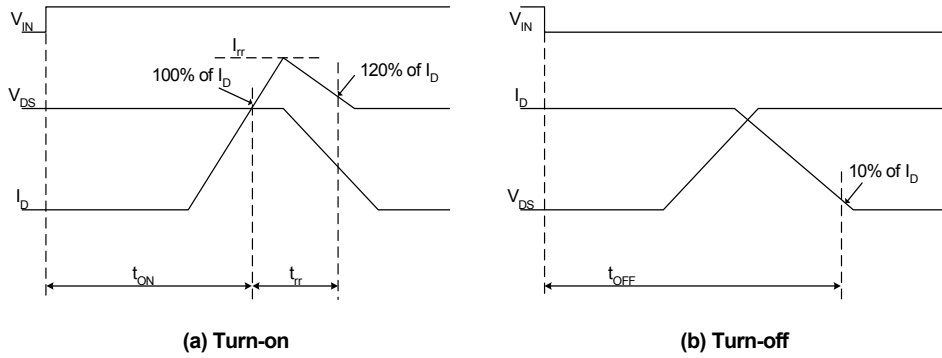


图 4. 开关时间定义

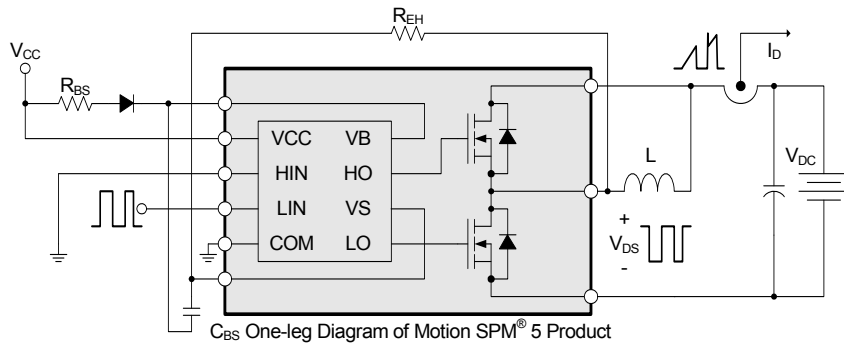


图 5. 开关和 RBSOA (单脉冲) 测试电路 (低端)

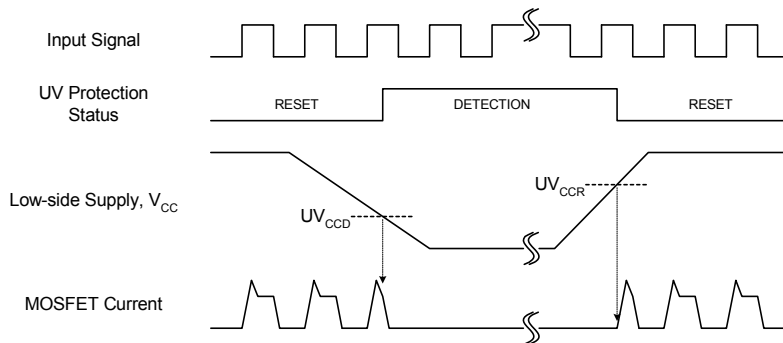


图 6. 欠压保护 (低端)

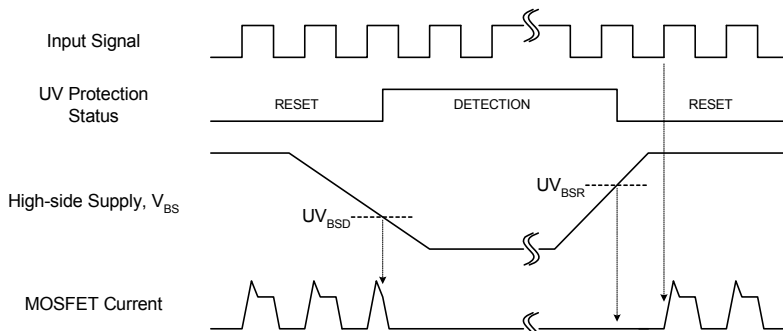


图 7. 欠压保护 (高端)

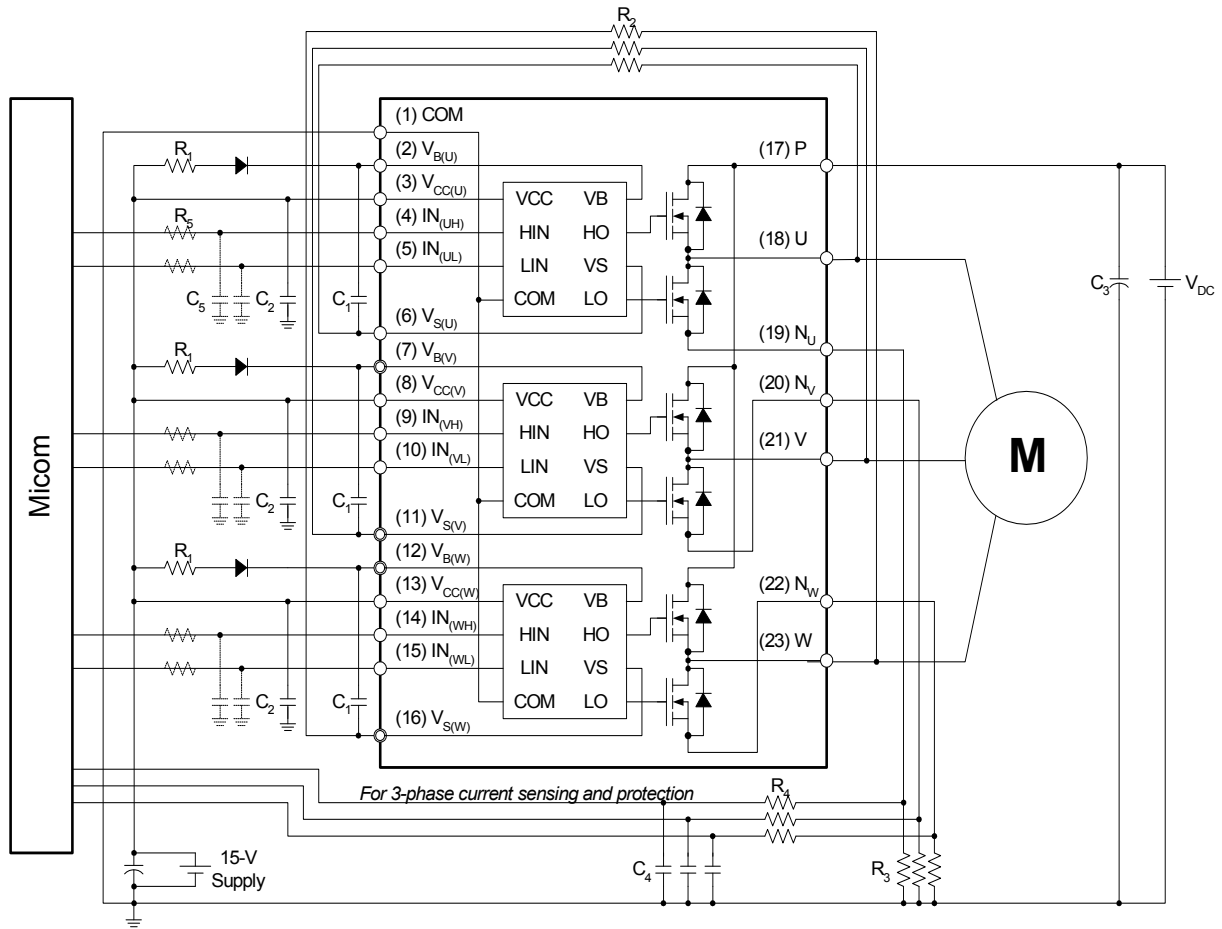
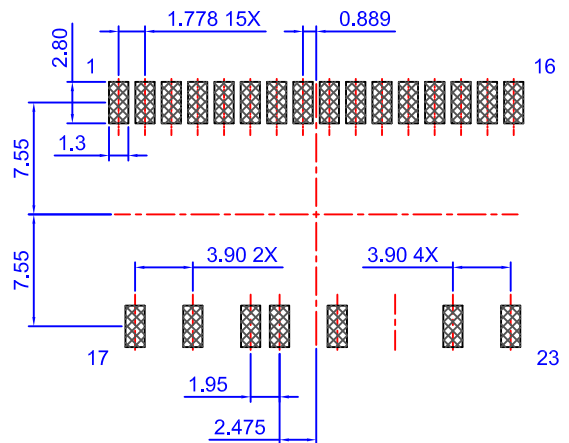
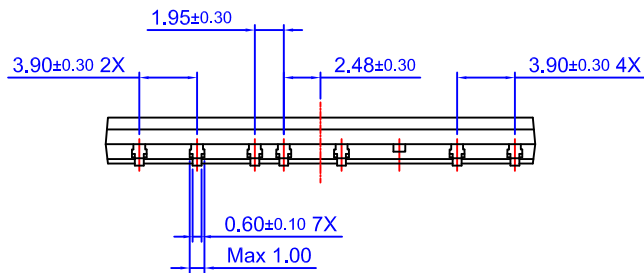
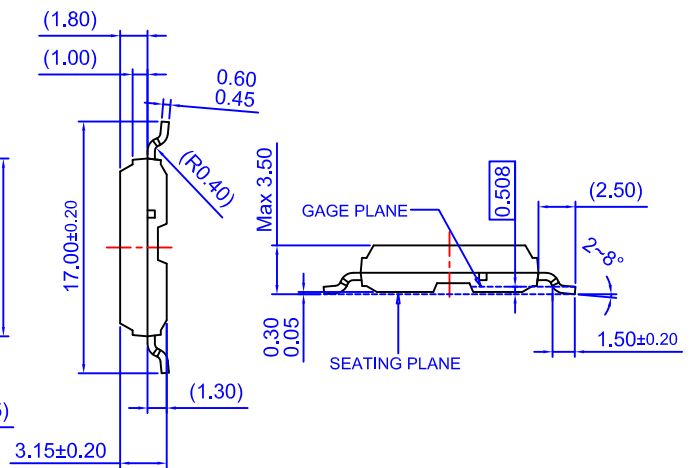
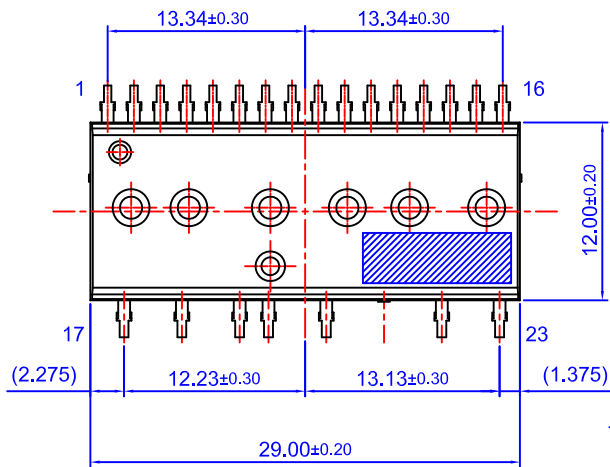
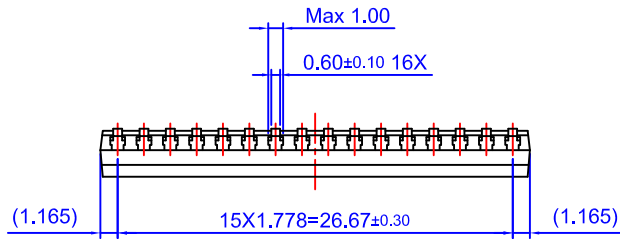


图 8. 应用电路实例

注:

1. 关于引脚的位置, 请参阅图 1。
2. Motion SPM® 5 产品和 MCU 的每个输入端的 RC 耦合 (R_5 和 C_5 , R_4 和 C_4) 能有效的防止由浪涌噪声产生的错误的输入信号。
3. 由于位于 COM 和低端 MOSFET 的源极端子之间, R_3 的压降会影响低端的开关性能和自举特性。为此, 稳态情况下 R_3 的压降应小于 1V。
4. 为避免浪涌电压和 HVIC 故障, 接地线和输出端子之间的接线应短且粗。
5. 所有的滤波电容器应紧密连接到 Motion SPM 5 产品, 它们应当具有能够很好的阻挡高频纹波电流的特性。



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